N-Channel Switch

J111, J112, J113, MMBFJ111, MMBFJ112, MMBFJ113

Features

- This Device is Designed for Low Level Analog Switching, Sample and Hold Circuits and Chopper Stabilized Amplifiers
- Sourced from Process 51
- Source & Drain are Interchangeable
- These are Pb-Free Devices

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted) (Note 1, 2)

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	35	V
V_{GS}	Gate-Source Voltage	-35	V
I _{GF}	Forward Gate Current	50	mA
T_J , T_{STG}	Operating and Storage Junction Temperature Range	–55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150 $^{\circ}\text{C}.$
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

THERMAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

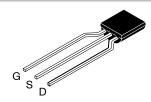
		Ma	ax	
Symbol	Parameter	J111 / J112 / J113 (Note 3)	MMBFJ111 / MMBFJ112 / MMBFJ113 (Note 4)	Unit
P _D	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	125	-	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	357	°C/W

- 3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
- Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm².

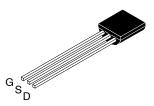


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TO-92 3 4.83x4.76 LEADFORMED CASE 135AR



TO-92 3 4.825x4.76 CASE 135AN

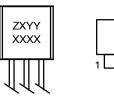


SOT-23 (TO-236) CASE 318-08



SOT-23 CASE 318BM

MARKING DIAGRAM





XX, XXXX = Z

Specific Device CodeAssembly Plant Code

XYY M = 3-Digit Date Code = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

	<u> </u>					
Symbol	Parameter	Test Conditi	ion	Min	Max	Unit
OFF CHARA	ACTERISTICS					
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_G = -1.0 \mu\text{A}, V_{DS} = 0$		-35	-	V
I _{GSS}	Gate Reverse Current	$V_{GS} = -15 \text{ V}, V_{DS} = 0$		-	-1.0	nA
V _{GS} (off)	Gate-Source Cut-Off Voltage	$V_{DS} = 5 \text{ V}, I_D = 1.0 \mu\text{A}$	111	-3.0	-10.0	V
			112	-1.0	-5.0	
			113	-0.5	-3.0	
I _D (off)	Drain Cutoff Leakage Current	$V_{DS} = 5.0 \text{ V}, V_{GS} = -10 \text{ V}$	V	-	1.0	nA
ON CHARA	CTERISTICS					
I _{DSS}	Zero-Gate Voltage Drain Current (Note 5)	V _{DS} = 15 V, V _{GS} = 0	111	20	_	mA
			112	5.0	_	1
			113	2.0	1	1
r _{DS} (on)	Drain-Source On Resistance	$V_{DS} \le 0.1 \text{ V, } V_{GS} = 0$	111	-	30	Ω
			112	-	50	1
			113	-	100	1
MALL SIG	NAL CHARACTERISTICS		•			
$C_{dg}(on) \ C_{sg}(on)$	Drain-Gate &Source-Gate On Capacitance	$V_{DS} = 0$, $V_{GS} = 0$, $f = 1.0$) MHz	_	28	pF
C _{dg} (off)	Drain-Gate Off Capacitance	V _{DS} = 0, V _{GS} = -10 V, f	= 1.0 MHz	-	5.0	pF
C _{sg} (off)	Source-Gate Off Capacitance	V _{DS} = 0, V _{GS} = -10 V, f =	= 1.0 MHz	-	5.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse test: pulse width ≤300 μs, duty cycle ≤2%.

TYPICAL PERFORMANCE CHARACTERISTICS

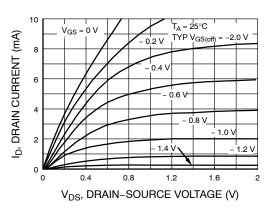


Figure 1. Common Drain-Source

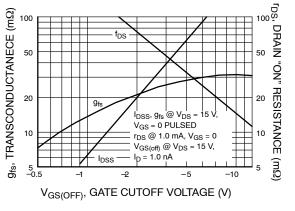


Figure 2. Parameter Interactions

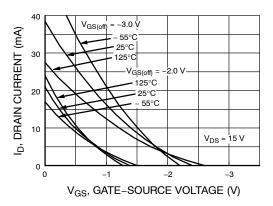


Figure 3. Transfer Characteristics

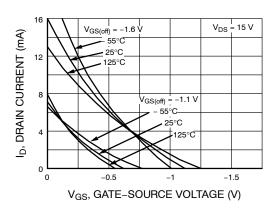


Figure 4. Transfer Characteristics

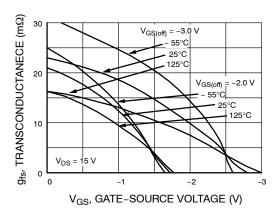


Figure 5. Transfer Characteristics

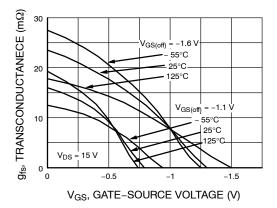


Figure 6. Transfer Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

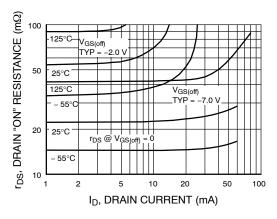


Figure 7. On Resistance vs. Drain Current

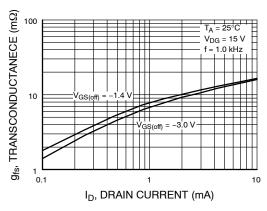


Figure 9. Transconductance vs. Drain Current

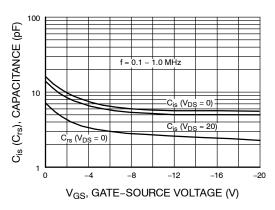


Figure 11. Capacitance vs. Voltage

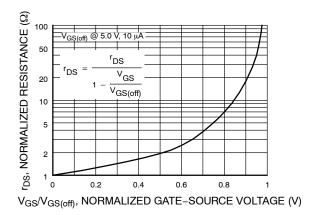


Figure 8. Normalized Drain Resistance vs.
Bias Voltage

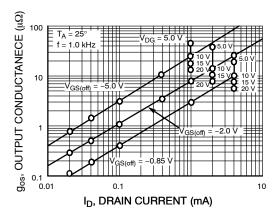


Figure 10. Output Conductance vs. Drain Current

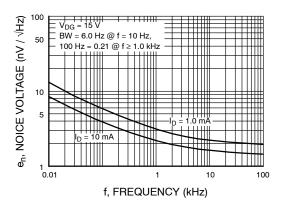


Figure 12. Noise Voltage vs. Frequency

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

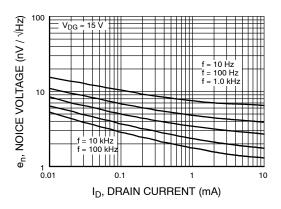


Figure 13. Noise Voltage vs. Current

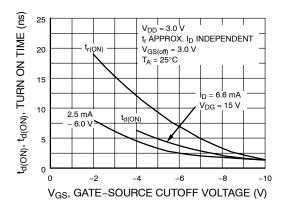


Figure 15. Switching Turn-On Time vs. Gate-Source Voltage

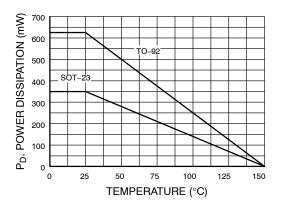


Figure 14. Power Dissipation vs.
Ambient Temperature

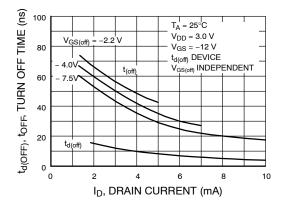


Figure 16. Switching Turn-Off Time vs.
Drain Current

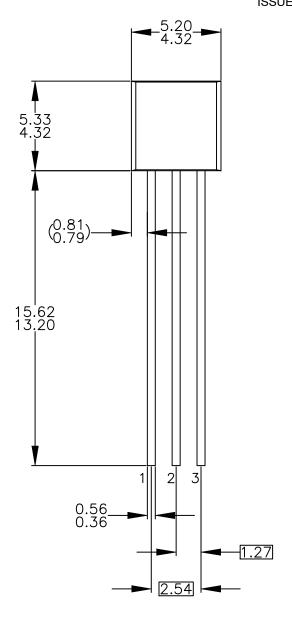
ORDERING INFORMATION

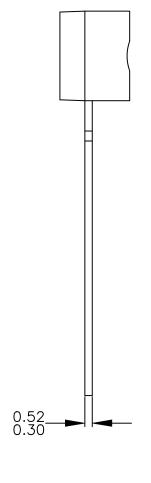
Part Number	Top Mark	Package	Shipping [†]
J111	J111	TO-92 3L (Pb-Free)	10000 Units / Bulk
J111-D26Z	J111	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J111-D74Z	J111	TO-92 3L (Pb-Free)	2000 / Ammo
J112	J112	TO-92 3L (Pb-Free)	10000 Units / Bulk
J112-D26Z	J112	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J112-D27Z	J112	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J112-D74Z	J112	TO-92 3L (Pb-Free)	2000 / Ammo
J113	J113	TO-92 3L (Pb-Free)	10000 Units / Bulk
J113-D74Z	J113	TO-92 3L (Pb-Free)	2000 / Ammo
MMBFJ111	6P	SOT-23 3L (Pb-Free)	3000 / Tape & Reel
MMBFJ112	6R	SOT-23 3L (Pb-Free)	3000 / Tape & Reel
MMBFJ113	6S	SOT-23 3L (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TO-92 3 4.825x4.76 CASE 135AN ISSUE O

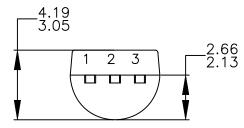
DATE 31 JUL 2016





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- ALL DIMENSIONS ARE IN MILLIMETERS.
 DRAWING CONFORMS TO ASME Y14.5M—2009.



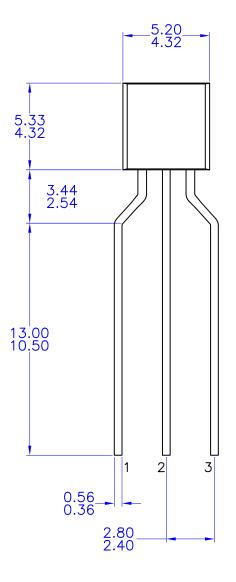
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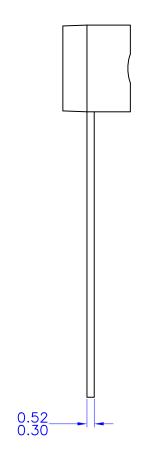
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CASE 135AR ISSUE O

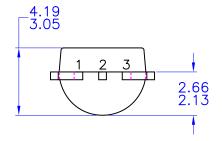
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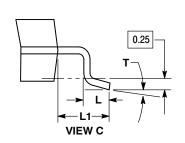


SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

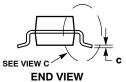
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

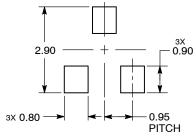
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

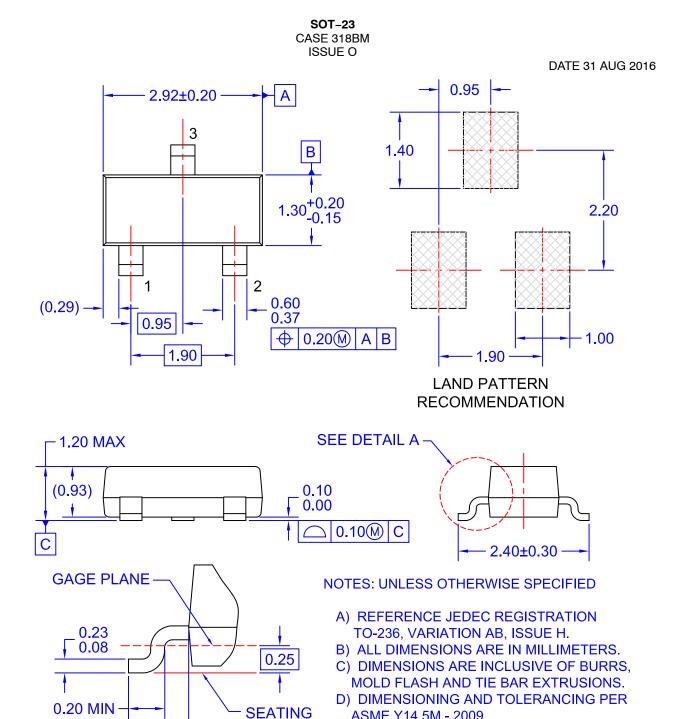
STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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3. CATHODE





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